

2-input OR Gate

REJ03D0196-0500Z (Previous ADE-205-306C (Z)) Rev.5.00 Jan.29.2004

## Description

The HD74HCT1G32 is high speed CMOS two input OR gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS–TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

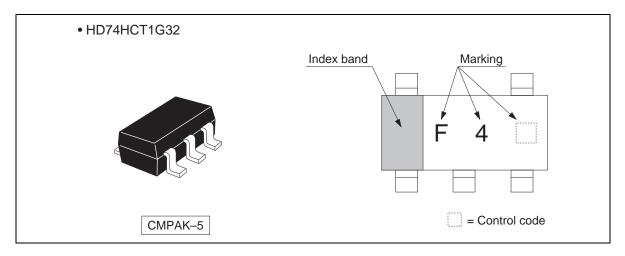
# Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- TTL compatible input level. Supply voltage range : 4.5 to 5.5 V Operating temperature range : -40 to +85°C
- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HCT1G32CME	CMPAK-5 pin	CMPAK-5V	СМ	E (3,000 pcs/reel)



## **Outline and Article Indication**



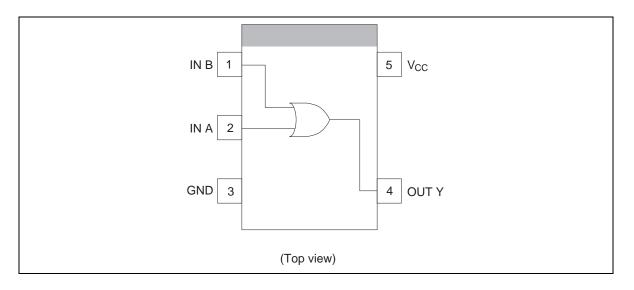
# **Function Table**

Inputs			
Α	В	Output Y	
L	L	L	
Н	L	Н	
L	Н	Н	
Н	Н	Н	

H : High level

L : Low level

# **Pin Arrangement**





### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V	
Input voltage range *1	VI	-0.5 to V <sub>CC</sub> + 0.5	V	
Output voltage range *1, 2	Vo	-0.5 to V <sub>CC</sub> + 0.5	V	Output : H or L
Input clamp current	I <sub>IK</sub>	±20	mA	$V_{I} < 0 \text{ or } V_{I} > V_{CC}$
Output clamp current	Ι <sub>ΟΚ</sub>	±20	mA	$V_0 < 0 \text{ or } V_0 > V_{CC}$
Continuous output current	lo	±25	mA	$V_0 = 0$ to $V_{CC}$
Continuous current through $V_{CC}$ or GND	$I_{CC}$ or $I_{GND}$	±25	mA	
Maximum power dissipation at Ta = 25°C (in still air) $^{*3}$	P <sub>T</sub>	200	mW	
Storage temperature	Tstg	–65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This value is limited to 5.5 V maximum.

3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Test Conditions
Supply voltage range	Vcc	4.5	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V <sub>CC</sub>	V	
Output current	IOL	_	2	mA	$V_{CC}$ = 4.5 to 5.5 V
	I <sub>OH</sub>		-2		$V_{CC}$ = 4.5 to 5.5 V
Input rise / fall time (0.3 V to 2.7 V)	t <sub>r</sub> , t <sub>f</sub>	0	500	ns	$V_{CC}$ = 4.5 to 5.5 V
Operating temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

## **Electrical Characteristics**

		Vcc	T <sub>a</sub> = 2	5°C		$T_a = -4$	T <sub>a</sub> = -40 to 85°C			
ltem	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Con	ditions
Input voltage	VIH	4.5 to 5.5	2.0			2.0	_	V		
	VIL	4.5 to 5.5	_	_	0.8	_	0.8	-		
Output voltage	V <sub>OH</sub>	4.5	4.4	4.5	—	4.4	—	V	V <sub>IN</sub> =	I <sub>OH</sub> = -20 μA
		4.5	4.18	4.31		4.13	—	-	$V_{\text{IH}} \text{ or } V_{\text{IL}}$	I <sub>ОН</sub> = -2 mA
	V <sub>OL</sub>	4.5	—	0.0	0.1	_	0.1	-		$I_{OL} = 20 \ \mu A$
		4.5	—	0.17	0.26	_	0.33	-		$I_{OL} = 2 \text{ mA}$
Input current	l <sub>IN</sub>	5.5	—	—	±0.1	—	±1.0	μΑ	$V_{IN} = V_{CC}$ or GND	
Operating current	I <sub>CC</sub>	5.5	_	_	1.0	_	10.0	μA	$V_{IN} = V_{CC} \text{ or } GND$	
Quiescent supply current	I <sub>CCT</sub>	5.5			2.0	_	2.9	mA	One input $V_{IN}$ = 2.4 V, other input $V_{CC}$ or GND	

# **Switching Characteristics**

		Ta = 25	°C				
Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Output rise / fall time	t <sub>⊤LH</sub> t <sub>⊤HL</sub>	_	5	10	ns	Test circuit	
Propagation delay time	t <sub>PLH</sub>	_	7.8	12	ns	Test circuit	
	t <sub>PHL</sub>	_	9.6	17			

 $(C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}, V_{CC} = 5 \text{ V})$ 

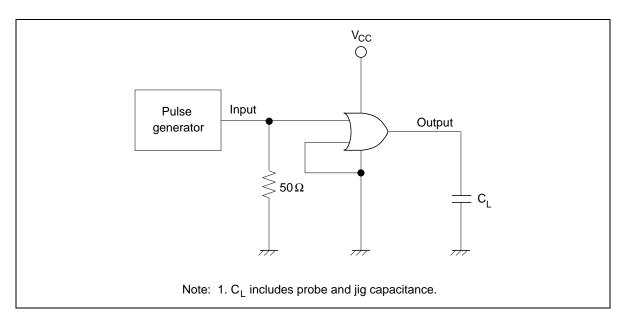
			Ta = 25°C			Ta = -40 to 85°C			
Item	Symbol	$V_{\text{cc}}$	Min	Тур	Max	Min	Max	Unit	Test Conditions
Output rise / fall time	t <sub>TLH</sub> t <sub>THL</sub>	4.5	_	14	25		31	ns	Test circuit
Propagation delay time	t <sub>PLH</sub>	4.5	_	10.5	16	—	20	ns	Test circuit
	t <sub>PHL</sub>	4.5	_	16.0	27	—	31	_	
Input capacitance	CIN	_	_	2.5	5	—	5	pF	
Equivalent capacitance	CPD			10			—	pF	

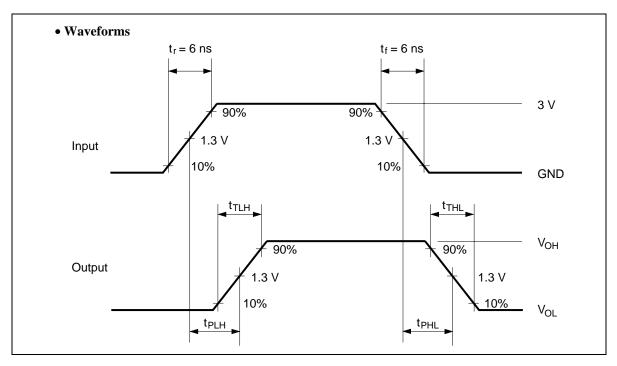
 $(C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$ 

Note: C<sub>PD</sub> is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

 $I_{CC} \text{ (opr)} = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$ 

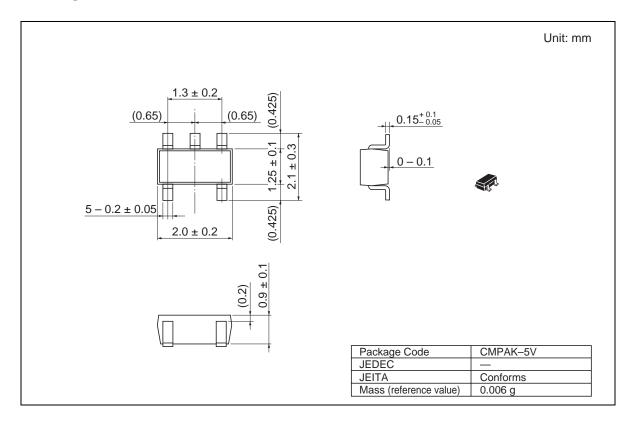
# **Test Circuit**







# **Package Dimensions**





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